

[SEMICONDUCTOR STRUCTURE AND FABRICATION THEREFOR]

Abstract

A semiconductor structure and a method of fabrication therefor are provided. The semiconductor structure comprises a substrate, a dielectric layer disposed over the substrate, a hydrophilic material layer disposed over the dielectric layer, and a hardmask layer disposed over the hydrophilic material layer. It is noted that, the edge of the semiconductor structure may be polished after the hydrophilic material layer is formed over the dielectric layer and before the hardmask layer is formed over the hydrophilic material layer.